PHI Quantes XPS/HAXPES Scanning Microprobe

HYSICA

DIVISION OF ULVAC-PH

TRONIC



- Patented XPS/HAXPES scanning microprobe technology
- In-situ analysis using soft (XPS) and hard (HAXPES) X-rays
- Cr X-rays offer 3x greater analysis depth vs. Al X-rays
- Cr X-rays offer access to higher energy core photoelectron peaks

- Patented dual beam charge neutralization for insulator analysis
- High performance spectroscopy and sputter depth profiling
- Fully integrated, high throughput surface analysis



25nm SiO, Film on Si Substrate

D PHYSICAL ELECTRONICS Al Kα = 1486.6 eV Cr Kα = 5414.9 eV a division of **ulvac-phi** Cr Ka ΑΙ Κα LaB₆ Scanning **Electron Source** Access to Deeper Core Photoelectron Peaks Open Lens Analyzer Design ΑΙ Κα 2p_{3/2} 3d Automated Range Ag Foil Dual Anode **XPS HAXPES** Normalized Intensity 2p_{1/2} Secondary Electron Imaging 3p1/2_3p3/2 with Scanning X-rays (SXI) 2s - LMM -- LMM

SmartSoft™ Instrument Control with Intuitive and Simple Workflow

5000

50 um

4000



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2000

Binding Energy (eV)

1000

n

3000